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| Form 1449* | Atty. Docket No.: 303.229US2 | Serial No. Unknown |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) | Applicant: Leonard Forbes | |
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| Examiner <u>Prematy</u> | Date Considered <u>10/98</u> |
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*Substitute Disclosure Statement Form (PTO-1449)

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